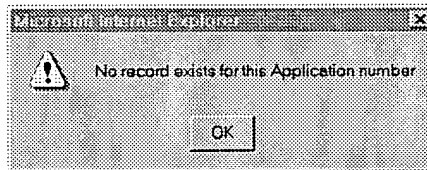


Electronic Information Disclosure Statement

US Document Identifiers Search Page

Application Number 10020813

SEARCH



9/12/04 Craig A. Thompson



Search History

DATE: Sunday, September 12, 2004

<u>Set</u> <u>Name</u>	<u>Query</u>	<u>Hit</u> <u>Count</u>	<u>Set</u> <u>Name</u> result set
side by side			
DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=ADJ			
<u>L20</u>	L19 and l8	25	<u>L20</u>
<u>L19</u>	single crystal near3 substrate	26742	<u>L19</u>
<u>L18</u>	"1000 .degree. C "	0	<u>L18</u>
<u>L17</u>	"1000.degree. C"	0	<u>L17</u>
<u>L16</u>	L15 and l8	2	<u>L16</u>
<u>L15</u>	(diffuse or diffusing) near5 dopant near9 (heat or heating or thermal or thermally or anneal or annealing or heated or annealed)	2488	<u>L15</u>
<u>L14</u>	l8 and L13	0	<u>L14</u>
<u>L13</u>	1000 C	19396	<u>L13</u>
<u>L12</u>	l8 and L11	34	<u>L12</u>
<u>L11</u>	1000	883307	<u>L11</u>
<u>L10</u>	".deg. "	0	<u>L10</u>
<u>L9</u>	".deg.C "	0	<u>L9</u>
<u>L8</u>	l5 and l6 and L7	64	<u>L8</u>
<u>L7</u>	pn junction or p-n junction or "p/N junction"	55504	<u>L7</u>
<u>L6</u>	semiconductor or substrate or wafer	2783133	<u>L6</u>
<u>L5</u>	L4 and @pd<20011212	156	<u>L5</u>
<u>L4</u>	l1 l2	215	<u>L4</u>
<u>L3</u>	l1 l2L2	0	<u>L3</u>
<u>L2</u>	"atoms/cm.sup.2 "	5318	<u>L2</u>
<u>L1</u>	"10.sup.13 "	8873	<u>L1</u>

END OF SEARCH HISTORY

9/12/04

Craig A. Thompson